

SPECIFICATION OF INFRARED LED CHIP

C800-40P

[INFRARED]

1) Commodity Type and Physical Characteristics.

1. Material	GaAlAs/GaAlAs(DDH)		
2. Electrode	Top Side	N (cathode)side	: Au Alloy
	Bottom Side	P (anode)side	: Au Alloy
3. Electrode Pattern	Fig.1		
4. Chip Size	Fig.2		
5. Chip Thickness	Fig.2		
6. Emission Area	Fig.2		

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V _f	I _f =20mA		1.50	1.70	V
Reverse Current	I _r	V _r =5V			10	μA
Power Intensity	P _o	I _f =20mA	2.5	4.0		mW
Peak Wavelength	λ _p	I _f =20mA	780	800	820	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		35		nm
RiseTime	t _r	I _f =20mA		80		ns
FallTime	t _f	I _f =20mA		80		ns

‡Die shall be mounted on TO-18 gold header without resin coated.(Ta=25°C)

[Unit : μm]

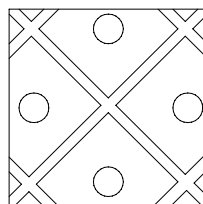
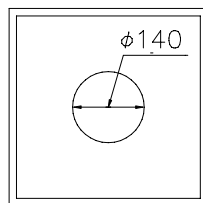


Fig.1 Electrode Pattern

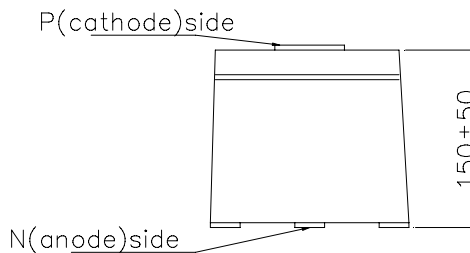
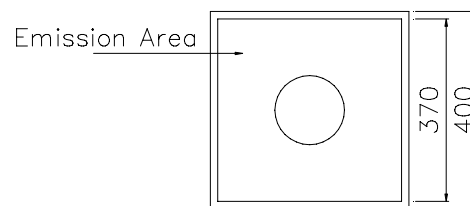


Fig.2 Chip size and Emission Area